

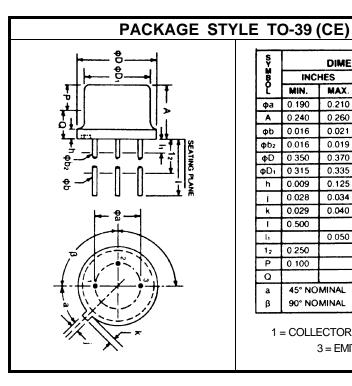
NPN SILICON HIGH FREQUENCY TRANSISTOR

DESCRIPTION:

The **TP2314** is a High Frequency Transistor Designed for Large Signal Power Amplifier Applications, With Emitter Grounded to Case.

MAXIMUM RATINGS

ı	1.0 A			
٧	18 V			
P _{DISS}	$8.0 \text{ W } @ \text{T}_{\text{C}} = 25 {}^{\text{O}}\text{C}$			
TJ	-65 °C to +200 °C			
T _{STG}	-65 °C to +200 °C			
¶JC	22 ^O C/W			



S	DIMENSIONS					
M B O	INCHES		MILLIMETERS			
የ	MIN.	MAX.	MIN.	MAX.		
фа	0.190	0.210	4.83	5.33		
Α	0.240	0.260	6.10	6.60		
фb	0.016	0.021	0.406	0.533		
φb₂	0.016	0.019	0.406	0.483		
φD	0.350	0.370	8.89	9.40		
φDı	0.315	0.335	8.00	8.51		
h	0.009	0.125	0.229	3.18		
i	0.028	0.034	0.711	0.864		
k	0.029	0.040	0.737	1.02		
	0.500		12.70			
lı.		0.050		1.27		
12	0.250		6.35			
Р	0.100		2.54			
a						
а	45° NO	MINAL				
β	90° NO	MINAL	l			

1 = COLLECTOR 2 = BASE3 = EMITTER

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CEO}	$I_C = 10 \text{ mA}$	18			٧
BV _{CES}	$I_{C} = 5.0 \text{ mA}$	36			٧
BV _{CBO}	$I_{C} = 5.0 \text{ mA}$	36			٧
I _{CBO}	V _{CB} = 15 V			250	Anne
BV _{EBO}	$I_E = 1.0 \text{ mA}$	4.0			V
h _{FE}	$V_{CE} = 5.0 \text{ V}$ $I_{C} = 250 \text{ mA}$	5.0			
C _{ob}	V _{CB} = 15 V f = 1.0 MHz	:		20	pF
G _{PE}	V _{CC} = 12.5 V P _{out} = 40 W f = 175 MH.	z 50		0.1	W %

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